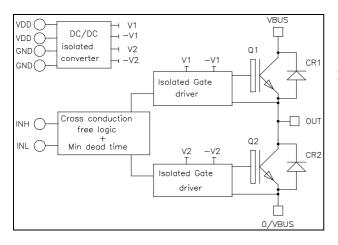
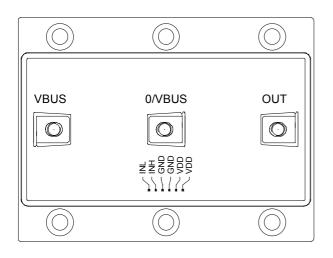


Phase leg Intelligent Power Module





APTLGT300A1208G

$V_{CES} = 1200V$ $I_{C} = 300A$ @ $Tc = 80^{\circ}C$

Application

- Motor control
- Uninterruptible Power Supplies
- Switched Mode Power Supplies
- Amplifier

Features

• Trench + Field Stop IGBT 3 Technology

- Low voltage drop
- Low tail current
- Soft recovery parallel diodes
- Low diode VF
- Low leakage current
- RBSOA and SCSOA rated
- Integrated Fail Safe IGBT Protection (Driver)
 - Top Bottom input signals Interlock
 - Isolated DC/DC Converter
- Low stray inductance
- M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Very high noise immunity (common mode rejection > 25kV/µs)
- Galvanic Isolation: 3750V for the optocoupler 2500V for the transformer
- 5V logic level with Schmitt-trigger Input
- Single V_{DD} =5V supply required
- Secondary auxiliary power supplies internally generated (15V, -6V)
- Optocoupler qualified to AEC-Q100 test guidelines
- RoHS compliant

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

1. Inverter Power Module

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	440	
I _C	T _c		300	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1400	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	600A @ 1150V	

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_j = 25^{\circ}C$			500	μA
		$V_{CE} = 1200V$	$T_{j} = 125^{\circ}C$			750	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{DD} = V_{IN} = 5V$	$T_j = 25^{\circ}C$		1.7	2.1	V
		$I_{\rm C} = 300 {\rm A}$	$T_{j} = 125^{\circ}C$		2		v

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		21		
C _{oes}	Output Capacitance	$V_{CE} = 25V$		1.12		nF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz		0.96		
T _r	Rise Time	Inductive Switching (25°C) $V_{c} = V_{c} = 5V_{c}$		40		ns
$T_{\rm f}$	Fall Time	$V_{DD} = V_{IN} = 5V$ $V_{Bus} = 600V$; $I_C = 300A$		70		ns
T _r	Rise Time	Inductive Switching (125°C)		45		20
$T_{\rm f}$	Fall Time	$V_{DD} = V_{IN} = 5V$		90		ns
Eon	Turn-on Switching Energy	$V_{Bus} = 600V$ $I_C = 300A$		28		
E_{off}	Turn-off Switching Energy			32		mJ
I _{sc}	Short Circuit data	$V_{DD} = V_{IN} = 5V; V_{Bus} = 900V$ $t_p \le 10 \mu s; T_j = 125^{\circ}C$		1200		А
R _{thJC}	Junction to Case thermal resistance				0.09	°C/W



Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_i = 25^{\circ}C$ $T_i = 125^{\circ}C$			250 500	μΑ
I _F	DC Forward Current		$Tc = 80^{\circ}C$		300		Α
V	Diode Forward Voltage	$I_{\rm F} = 300 {\rm A}$	$T_i = 25^{\circ}C$		1.6	2.1	V
$V_{\rm F}$			$T_{i} = 125^{\circ}C$		1.6		v
t _{rr}	Reverse Recovery Time	Т	$T_j = 25^{\circ}C$		170		ns
ι _{rr}			$T_{j} = 125^{\circ}C$		280		115
Q _{rr}	Reverse Recovery Charge	$I_F = 300A$ $V_R = 600V$ $di/dt = 3500A/\mu s$	$T_j = 25^{\circ}C$		28		μC
Qrr	Reverse Recovery Charge		$T_{i} = 125^{\circ}C$		56		μΟ
Г			$T_i = 25^{\circ}C$		12		T
E _{rr}	Reverse Recovery Energy		$T_{j} = 125^{\circ}C$		22		mJ
R _{thJC}	Junction to Case Thermal Resistance					0.16	°C/W

2. Driver

Absolute maximum ratings

Symbol		Parameter	Max ratings	Unit
V_{DD}	Supply Voltage		5.5	V
V _{INi}	Input signal voltage i=L, H		5.5	v
т	Maximum Supply current $\frac{V_{INi} = 0V, i = L \& H}{V_{DD} = 5V, V_{INH} = /V_{INL}; F_{out} = 45kHz}$	$V_{INi} = 0V, i = L \& H$	0.35	
I _{VDDmax}		2	A	
\mathbf{f}_{max}	Maximum Switching Frequen	cy	45	kHz

Driver Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
V _{DD}	Operating Supply Voltage		4.5	5	5.5	V
V _{INi(max)}	Maximum Input Voltage		-0.5	5	5.5	
V _{INi (th+)}	Positive Going Threshold Voltage	i = L, H		3.2		V
V _{INi(th-)}	Negative Going Threshold Voltage	1 2,11		1		
R _{INi}	Input Resistance *	1		1		kΩ
T _{d(on)}	Turn On delay time	Driver + IGBT		1100 ⁰		
D _T	Built in dead time			600		ns
T _{d(off)}	Turn Off delay time	Driver + IGBT		750		
PWD	Pulse Width Distortion				300	
PDD	Propagation Delay Difference between any two driver	T _{d(on)} - T _{d(off)}	-350		350	ns
V _{ISOL}	Primary to Secondary Isolation		2500			V_{RMS}

* Low impedance guarantees good noise immunity.

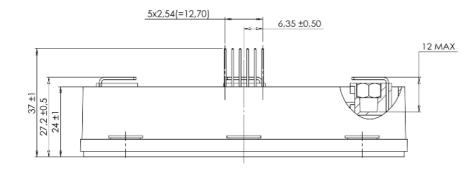
• Including built in dead time.

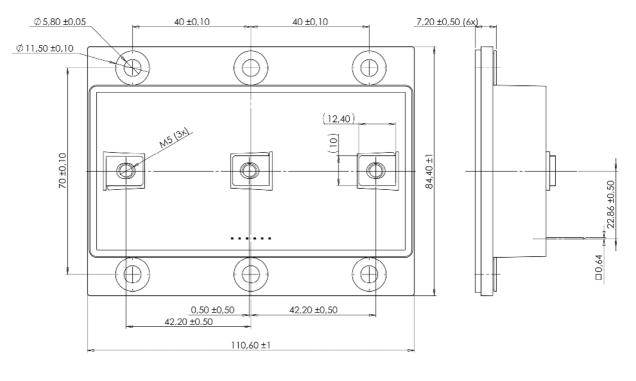


3. Package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =	1 min, 50/60Hz		4000			V		
T _J	Operating junction temperature range			-40		150			
T _{OP}	Operating Ambient Temperature			-40		85	°C		
T _{STG}	Storage Temperature Range			-40		100	C		
T _C	Operating Case Temperature			-40		100			
Torque	Mounting torque	To heatsink	M5	2		4.7	N.m		
Torque	Mounting torque For terminals M5		M5	2		4	IN.III		
Wt	Package Weight				550		g		

4. LP8 Package outline (dimensions in mm)

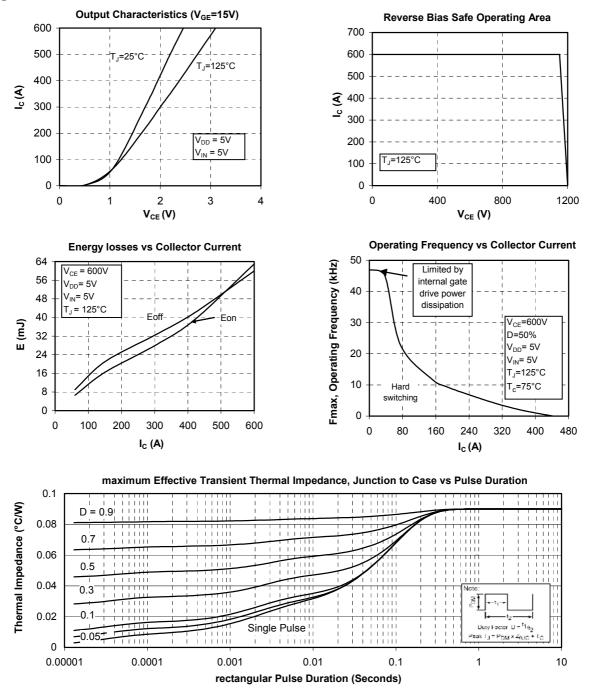




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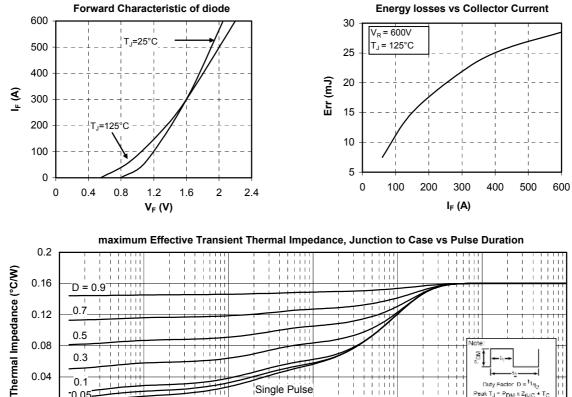
Typical IGBT Performance Curve

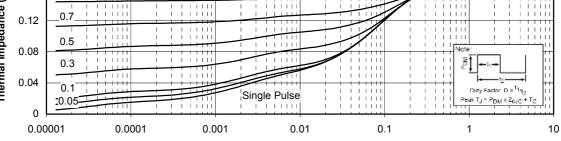


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Typical diode Performance Curve





rectangular Pulse Duration (Seconds)



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